

isc N-Channel MOSFET Transistor

4N90

- **DESCRIPTION**
- Drain Current $I_D = 3.6A @ T_C = 25^{\circ}C$
- Drain Source Voltage-
: $V_{DSS} = 900V (Min)$
- Fast Switching Speed

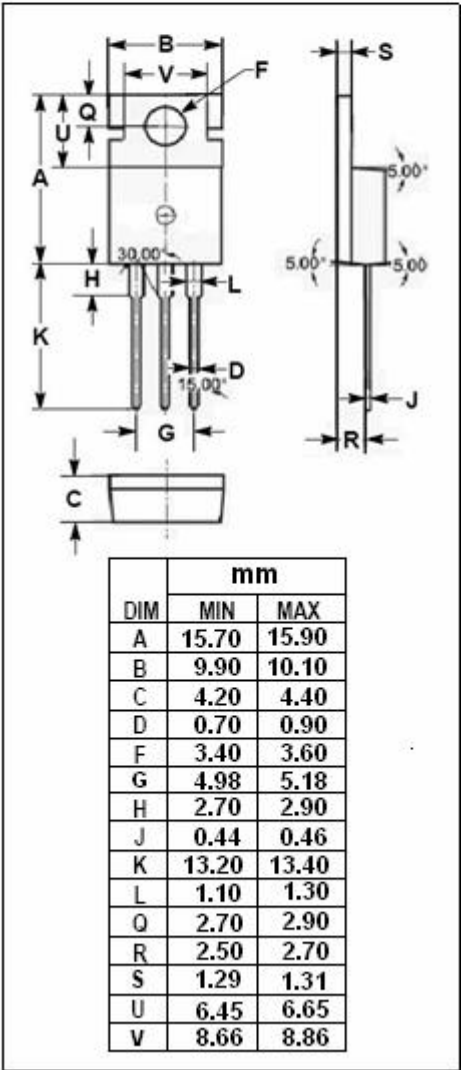
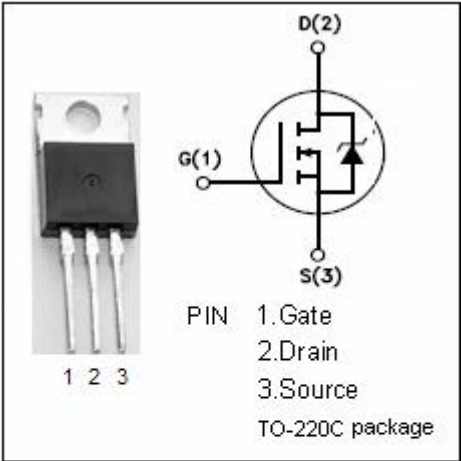
- **APPLICATIONS**
- General purpose power amplifier

ABSOLUTE MAXIMUM RATINGS($T_C = 25^{\circ}C$)

SYMBOL	ARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage ($V_{GS} = 0$)	900	V
V_{GS}	Gate-Source Voltage	± 30	V
I_D	Drain Current-continuous@ $T_C = 25^{\circ}C$	3.6	A
$I_{D(puls)}$	Pulse Drain Current	11	A
P_{tot}	Total Dissipation@ $T_C = 25^{\circ}C$	100	W
T_j	Max. Operating Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature Range	-55~150	$^{\circ}C$

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	0.96	$^{\circ}C/W$
$R_{th\ j-a}$	Thermal Resistance, Junction to Ambient	62.5	$^{\circ}C/W$



isc N-Channel MOSFET Transistor**4N90**• ELECTRICAL CHARACTERISTICS ($T_C=25^{\circ}\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0; I_D=250\mu\text{A}$	900			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}; I_D=250\mu\text{A}$	2.0		4.0	V
V_{SD}	Diode Forward On-Voltage	$I_F=4\text{A}; V_{GS}=0$			1.4	V
$R_{DS(on)}$	Drain-Source On-Resistance	$V_{GS}=10\text{V}; I_D=1.7\text{A}$			3.5	Ω
I_{GSS}	Gate-Body Leakage Current	$V_{GS}=\pm 30\text{V}; V_{DS}=0$			± 100	nA
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=900\text{V}; V_{GS}=0$			25	μA